

Investigation of strain relaxation mechanism in Si-SiO₂ system during the process of its formation

Kropman, Daniel; Poll, V.; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; Arbu, Uno; Paomets, V. Physica status solidi (a) 2003 / 2, p. 297-301 <https://onlinelibrary.wiley.com/doi/abs/10.1002/pssa.200306611>

Point defects interaction with extended defects and impurities and its influence on the Si-SiO₂ system properties

Kropman, Daniel; Arbu, Uno; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; **Kauk, Marit**; Heinmaa, I.; **Samoson, Ago**; Medvid, A.

Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill

https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties